

PN2907A

Preferred Device

General Purpose Transistor PNP Silicon

Features

- These are Pb-Free Devices*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	-60	Vdc
Collector-Base Voltage	V_{CBO}	-60	Vdc
Emitter-Base Voltage	V_{EBO}	-5.0	Vdc
Collector Current - Continuous	I_C	-600	mAdc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	625 5.0	mW mW/ $^\circ\text{C}$
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	1.5 12	W mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	- 55 to +150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

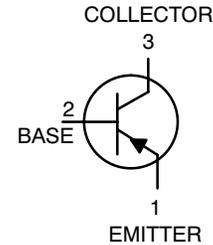
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction- to- Ambient	$R_{\theta JA}$	200	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	83.3	$^\circ\text{C}/\text{W}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

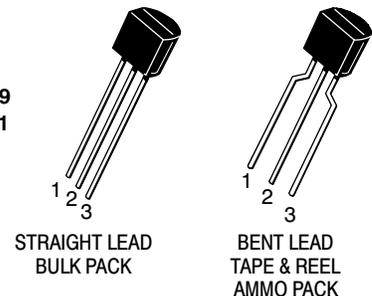


ON Semiconductor®

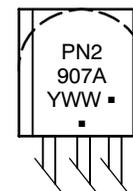
<http://onsemi.com>



TO-92
CASE 29
STYLE 1



MARKING DIAGRAM



PN2907A = Device Code
Y = Year
WW = Work Week
■ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 3 of this data sheet.

Preferred devices are recommended choices for future use and best overall value.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PN2907A

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage (Note 1) (I _C = -10 mA, I _B = 0)	V _{(BR)CEO}	-60	-	Vdc
Collector-Base Breakdown Voltage (I _C = -10 μA, I _E = 0)	V _{(BR)CBO}	-60	-	Vdc
Emitter-Base Breakdown Voltage (I _E = -10 μA, I _C = 0)	V _{(BR)EBO}	-5.0	-	Vdc
Collector Cutoff Current (V _{CE} = -30 Vdc, V _{EB(off)} = -0.5 Vdc)	I _{CEX}	-	-50	nAdc
Collector Cutoff Current (V _{CB} = -50 Vdc, I _E = 0) (V _{CB} = -50 Vdc, I _E = 0, T _A = 150°C)	I _{CBO}	-	-0.01 -10	μAdc
Base Current (V _{CE} = -30 Vdc, V _{EB(off)} = -0.5 Vdc)	I _B	-	-50	nAdc

ON CHARACTERISTICS

DC Current Gain (I _C = -0.1 mA, V _{CE} = -10 Vdc) (I _C = -1.0 mA, V _{CE} = -10 Vdc) (I _C = -10 mA, V _{CE} = -10 Vdc) (I _C = -150 mA, V _{CE} = -10 Vdc) (Note 1) (I _C = -500 mA, V _{CE} = -10 Vdc) (Note 1)	h _{FE}	75 100 100 100 50	- - - 300 -	-
Collector-Emitter Saturation Voltage (Note 1) (I _C = -150 mA, I _B = -15 mA) (I _C = -500 mA, I _B = -50 mA)	V _{CE(sat)}	- -	-0.4 -1.6	Vdc
Base-Emitter Saturation Voltage (Note 1) (I _C = -150 mA, I _B = -15 mA) (I _C = -500 mA, I _B = -50 mA)	V _{BE(sat)}	- -	-1.3 -2.6	Vdc

SMALL-SIGNAL CHARACTERISTICS

Current-Gain - Bandwidth Product (Notes 1 and 2), (I _C = -50 mA, V _{CE} = -20 Vdc, f = 100 MHz)	f _T	200	-	MHz
Output Capacitance (V _{CB} = -10 Vdc, I _E = 0, f = 1.0 MHz)	C _{obo}	-	8.0	pF
Input Capacitance (V _{EB} = -2.0 Vdc, I _C = 0, f = 1.0 MHz)	C _{ibo}	-	30	pF

SWITCHING CHARACTERISTICS

Turn-On Time	(V _{CC} = -30 Vdc, I _C = -150 mA, I _{B1} = -15 mA) (Figures 1 and 5)	t _{on}	-	45	ns
Delay Time		t _d	-	10	ns
Rise Time		t _r	-	40	ns
Turn-Off Time	(V _{CC} = -6.0 Vdc, I _C = -150 mA, I _{B1} = I _{B2} = 15 mA) (Figure 2)	t _{off}	-	100	ns
Storage Time		t _s	-	80	ns
Fall Time		t _f	-	30	ns

1. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.
2. f_T is defined as the frequency at which |h_{fe}| extrapolates to unity.

PN2907A

ORDERING INFORMATION

Device	Package	Shipping [†]
PN2907AG	TO-92 (Pb-Free)	5000 Units / Bulk
PN2907ARLRAG	TO-92 (Pb-Free)	2000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

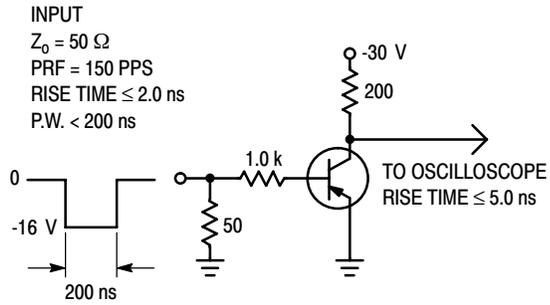


Figure 1. Delay and Rise Time Test Circuit

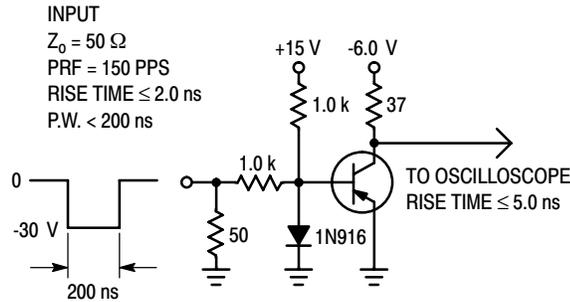


Figure 2. Storage and Fall Time Test Circuit

PN2907A

TYPICAL CHARACTERISTICS

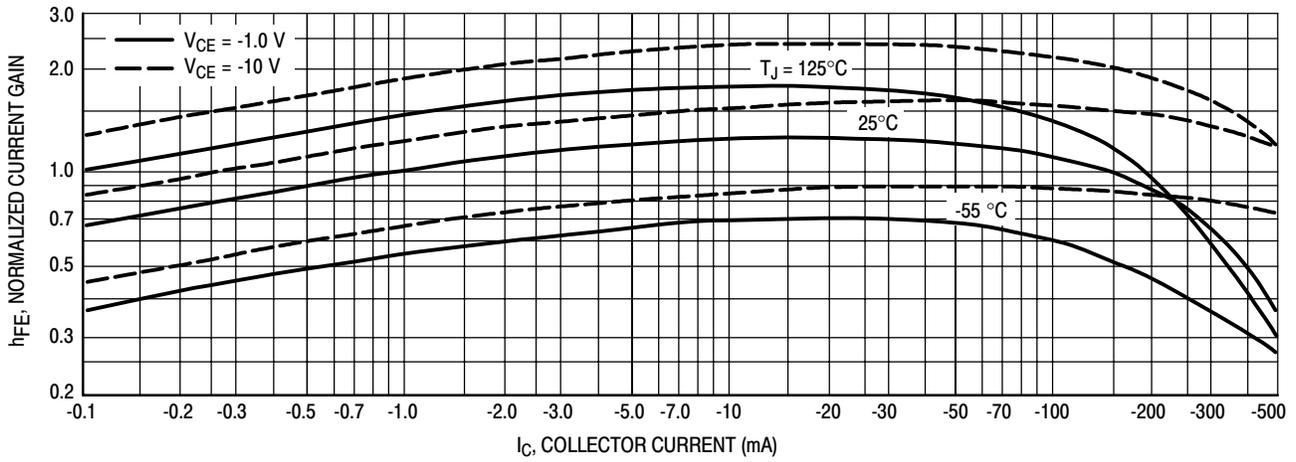


Figure 3. DC Current Gain

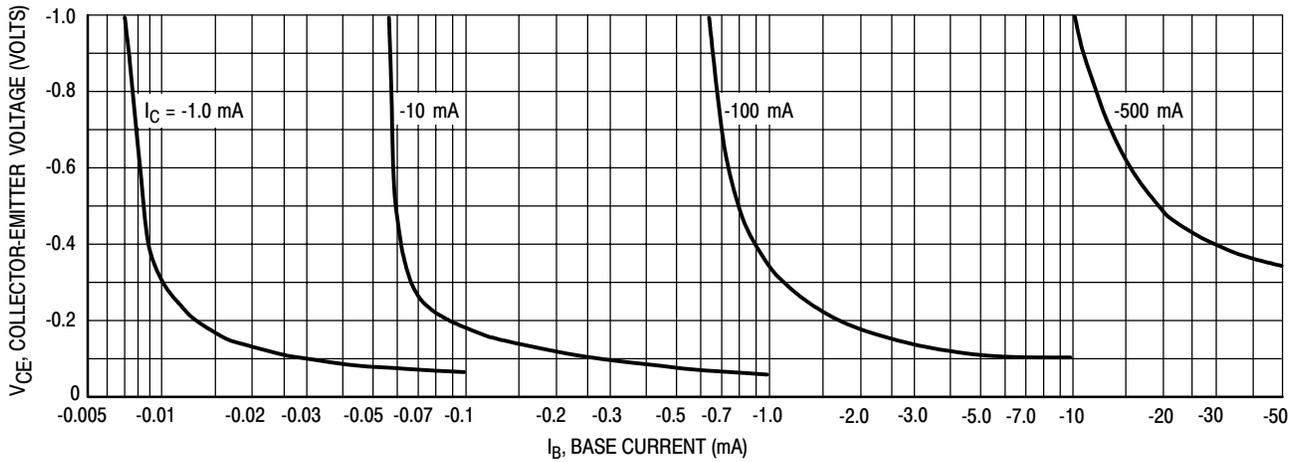


Figure 4. Collector Saturation Region

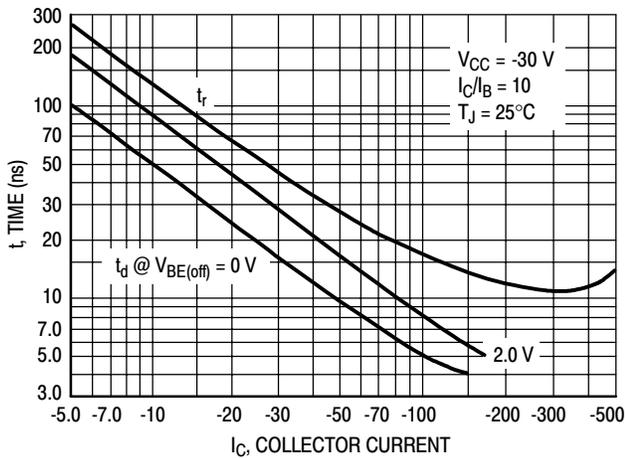


Figure 5. Turn-On Time

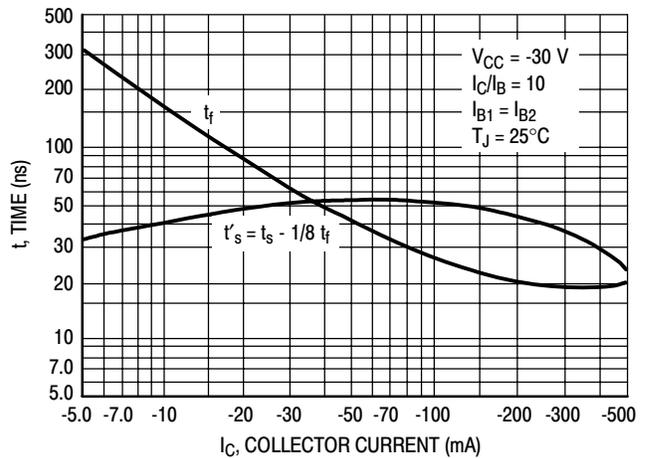


Figure 6. Turn-Off Time

PN2907A

TYPICAL SMALL-SIGNAL CHARACTERISTICS

NOISE FIGURE

$V_{CE} = 10 \text{ Vdc}$, $T_A = 25^\circ\text{C}$

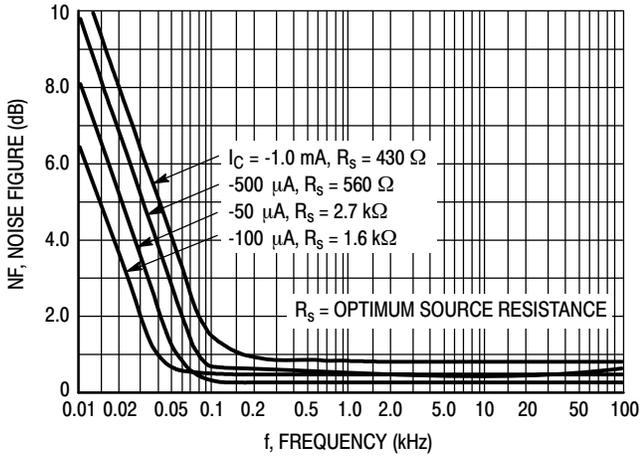


Figure 7. Frequency Effects

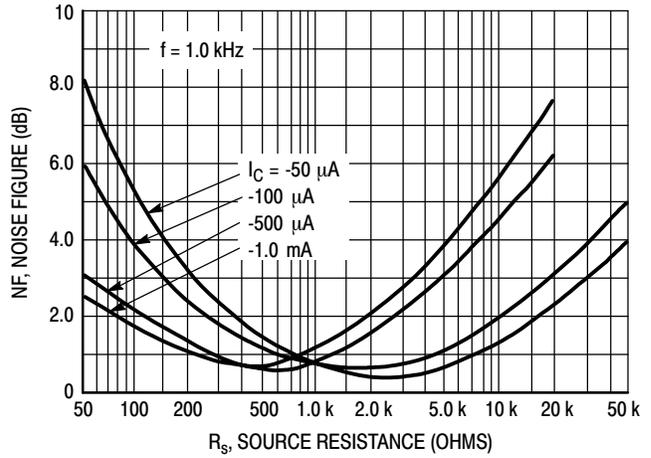


Figure 8. Source Resistance Effects

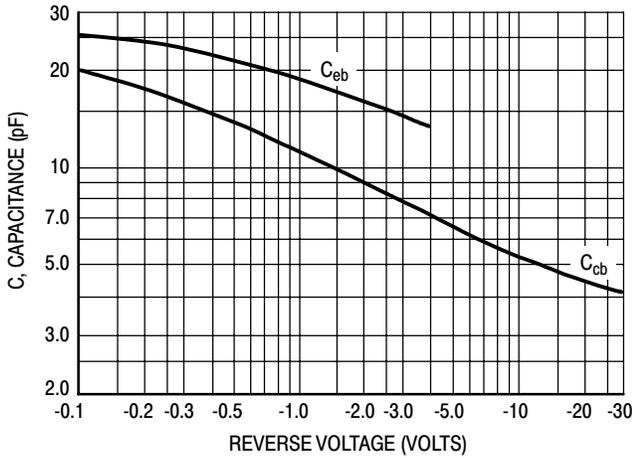


Figure 9. Capacitances

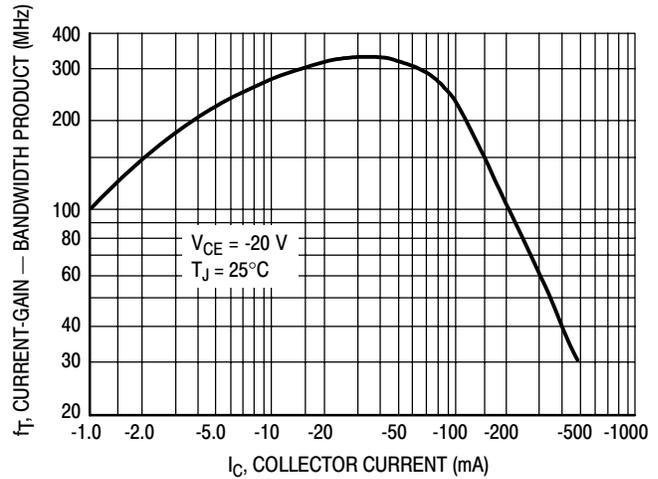


Figure 10. Current-Gain — Bandwidth Product

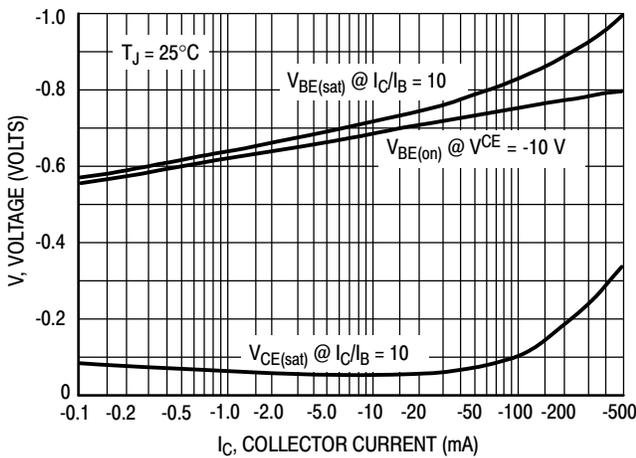


Figure 11. "On" Voltage

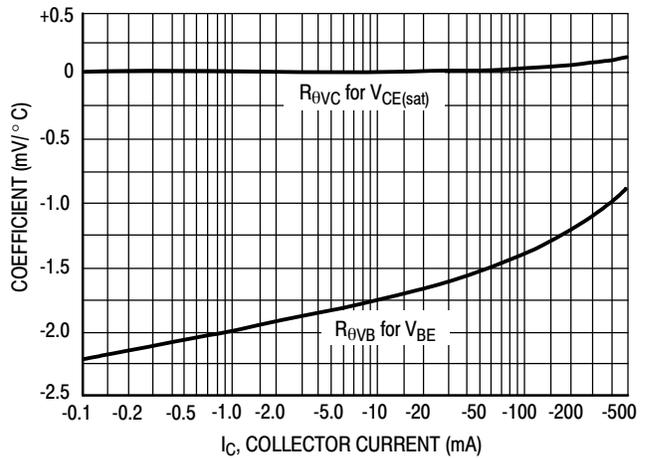
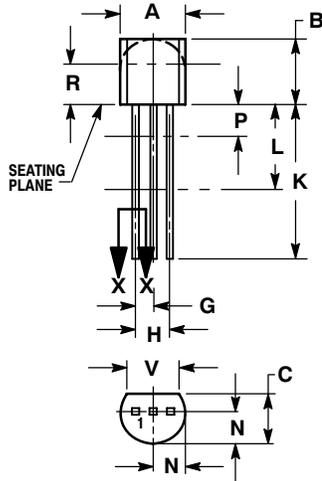


Figure 12. Temperature Coefficients

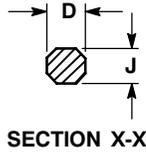
PN2907A

PACKAGE DIMENSIONS

TO-92 (TO-226)
CASE 29-11
ISSUE AM



STRAIGHT LEAD
BULK PACK

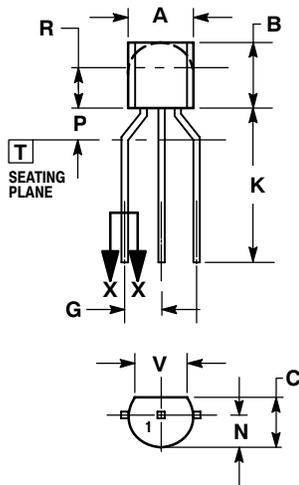


SECTION X-X

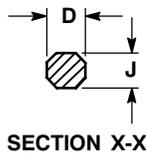
NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.175	0.205	4.45	5.20
B	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500	---	12.70	---
L	0.250	---	6.35	---
N	0.080	0.105	2.04	2.66
P	---	0.100	---	2.54
R	0.115	---	2.93	---
V	0.135	---	3.43	---



BENT LEAD
TAPE & REEL
AMMO PACK



SECTION X-X

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

DIM	MILLIMETERS	
	MIN	MAX
A	4.45	5.20
B	4.32	5.33
C	3.18	4.19
D	0.40	0.54
G	2.40	2.80
J	0.39	0.50
K	12.70	---
N	2.04	2.66
P	1.50	4.00
R	2.93	---
V	3.43	---

STYLE 1:

1. EMITTER
2. BASE
3. COLLECTOR

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